

Appl. No. 10/710,548
Amdt. Dated 06/13/2007
Reply to Office action of April 13, 2007

Amendments to the Specification:

In the specifications please replace paragraph 52 with the following paragraph:

Next, as shown in FIG. 4A, a layer 420 of silicon semiconductor material is deposited on the surface of mesa 412 and on isolation oxide 408 using a nonselective epitaxial deposition technique. The layer 420 deposits as a polycrystalline material on the oxide 408, as single crystal material on the surface of mesa 412, and as polysilicon on the thin polysilicon layer remaining over 416. The layer 420 is undoped. Included in the layer 420 is a thin portion which is doped to have a p-type conductivity. The layer 420 will form the base of the BJT. The layer 420 may also include an alloy of Silicon Germanium (SiGe) in order to form a heterojunction bipolar transistor (HBT). This layer 420 has a thickness of approximately 10-50 nm, over the mesa 412 (in the openings), and over the layers 416 and 418.